

GT04N65 Series

N-Channel Power Field Effect Transistor (650V, 4A)

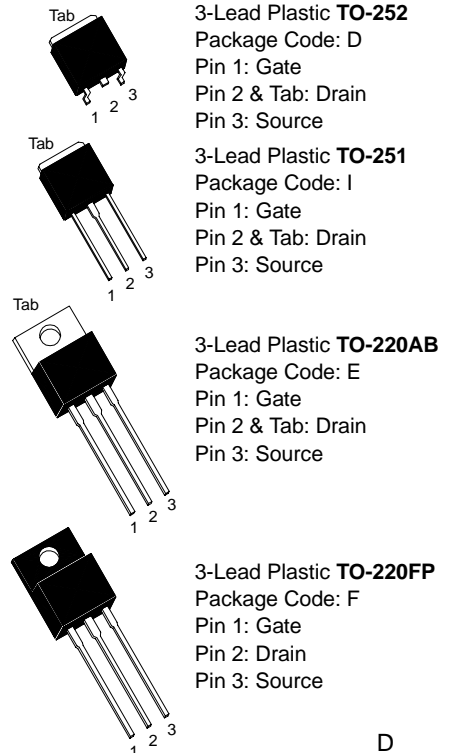
Description

This advanced high voltage MOSFET is designed to withstand high energy in the avalanche mode and switch efficiently. This new high energy device also offers a drain-to-source diode with fast recovery time. Designed for high voltage, high speed switching applications such as power supplies, converters, power motor controls and bridge circuits.

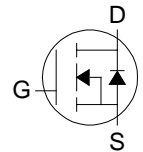
Features

- Higher Current Rating
- Lower $R_{DS(on)} < 3.0\Omega$ (@ $V_{GS}=10V, I_D=2A$)
- Lower Capacitances
- Lower Total Gate Charge
- Tighter VSD Specifications
- Avalanche Energy Specified

GT04N65 Series Pin Assignment



GT04N65 Series
 Symbol:



Absolute Maximum Ratings

Symbol	Parameter	Value	Units
I_D	Drain to Current (Continuous)	4	A
I_{DM}	Drain to Current (Pulsed)	16	A
V_{GS}	Gate-to-Source Voltage (Continue)	± 30	V
P_D	Total Power Dissipation ($T_C=25^\circ C$)		
	GT04N65I (TO-251) / GT04N65D (TO-252)	50	W
	GT04N65E (TO-220AB)	50	
	GT04N65F (TO-220FP)	25	
P_D	Derate above $25^\circ C$		
	GT04N65I (TO-251) / GT04N65D (TO-252)	0.4	$W/^\circ C$
	GT04N65E (TO-220AB)	0.4	
	GT04N65F (TO-220FP)	0.33	
T_j, T_{stg}	Operating and Storage Temperature Range	-55 to 150	$^\circ C$
E_{AS}	Single Pulse Drain-to-Source Avalanche Enrgy- $T_j=25^\circ C$ $(V_{DD}=100V, V_{GS}=10V, I_L=2A, L=10mH, R_G=25\Omega)$	35	mJ
T_L	Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	260	$^\circ C$

Thermal Characteristics

Symbol	Parameter	Value		Units
$R_{\theta JC}$	Thermal Resistance Junction to Case Max.	TO-251 / TO-252	2	°C/W
		TO-220AB	2	
		TO-220FL	3.3	
$R_{\theta JA}$	Thermal Resistance Junction to Ambient Max.	62.5		°C/W

Electrical Characteristics (T_j=25°C, unless otherwise specified)

Symbol	Characteristic	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage ($V_{GS}=0V, I_D=250\mu A$)	650	-	-	V
I_{DSS}	Drain-Source Leakage Current ($V_{DS}=650V, V_{GS}=0V$)	-	-	10	μA
	Drain-Source Leakage Current ($V_{DS}=480V, V_{GS}=0V, T_J=125^\circ C$)	-	-	50	μA
I_{GSSF}	Gate-Source Leakage Current-Forward ($V_{gsf}=30V, V_{DS}=0V$)	-	-	100	nA
I_{GSSR}	Gate-Source Leakage Current-Reverse ($V_{gsr}=-30V, V_{DS}=0V$)	-	-	-100	nA
$V_{GS(th)}$	Gate Threshold Voltage ($V_{DS}=V_{GS}, I_D=250\mu A$)	2	-	4	V
$R_{DS(on)}$	Static Drain-Source On-Resistance ($V_{GS}=10V, I_D=2A$)*	-	2.3	3.0	Ω
g_{FS}	Forward Transconductance ($V_{DS}=15V, I_D=2A$)*	2	-	-	Mhos
C_{iss}	Input Capacitance	-	670.5	-	pF
C_{oss}	Output Capacitance	-	51.1	-	
C_{rss}	Reverse Transfer Capacitance	-	4.8	-	
$t_{d(on)}$	Turn-on Delay Time	-	20	-	Ns
t_r	Rise Time	-	19	-	
$t_{d(off)}$	Turn-off Delay Time	-	128	-	
t_f	Fall Time	-	20	-	
Q_g	Total Gate Charge	-	16.9	-	nC
Q_{gs}	Gate-Source Charge	-	3.3	-	
Q_{gd}	Gate-Drain Charge	-	6.9	-	

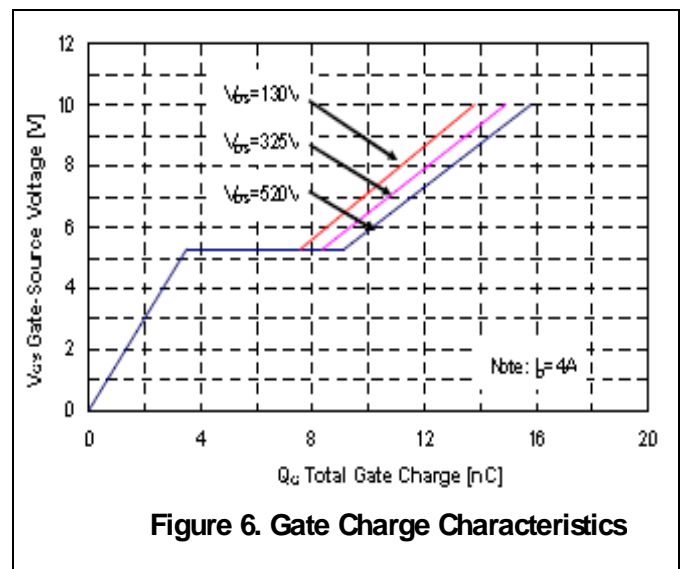
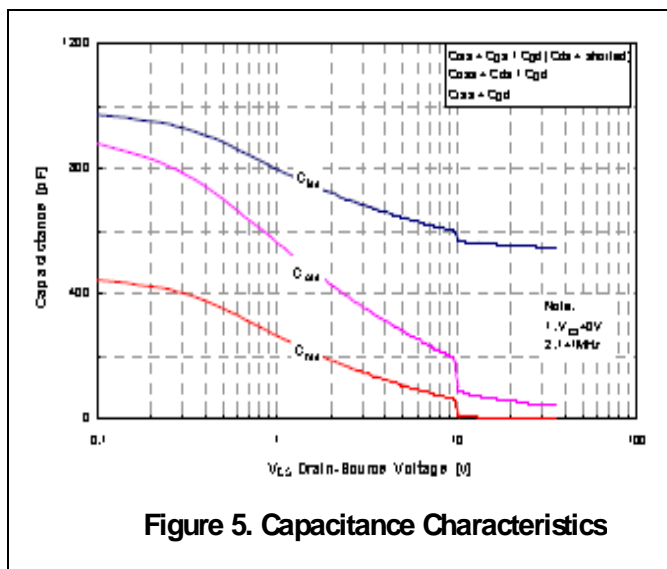
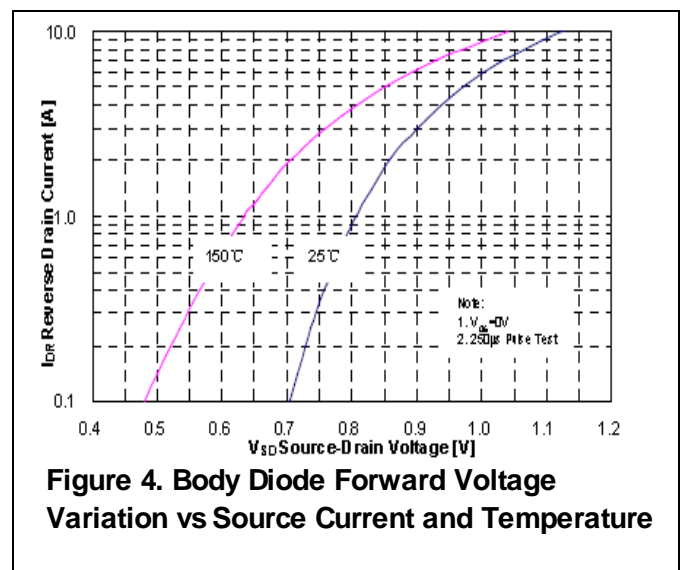
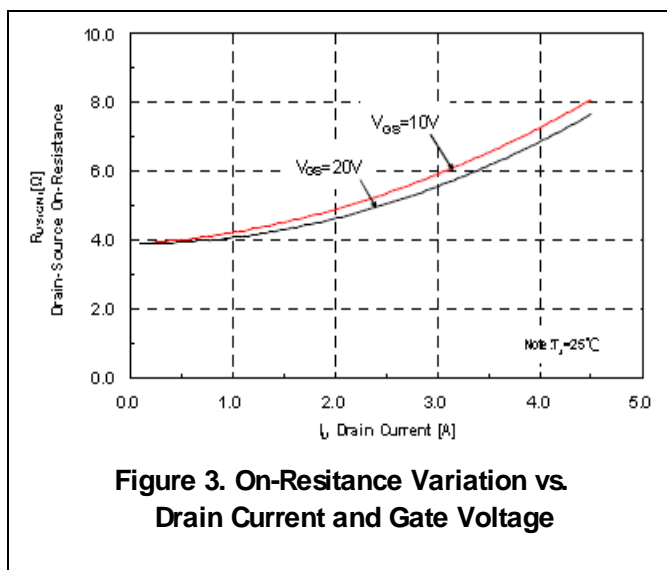
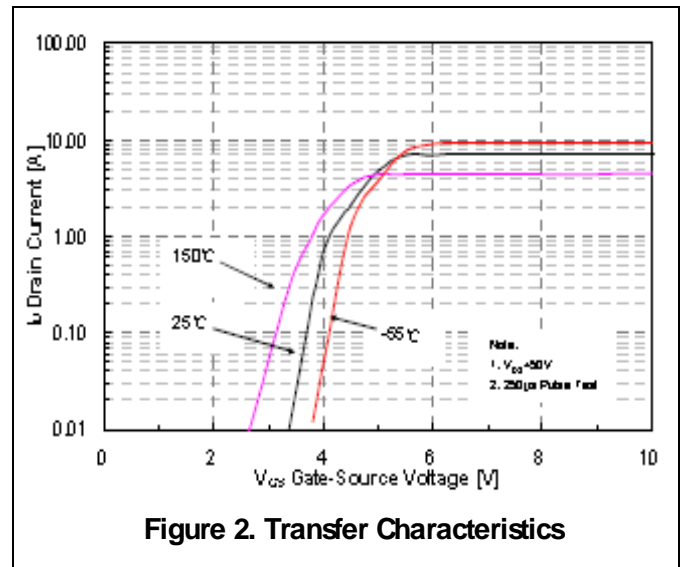
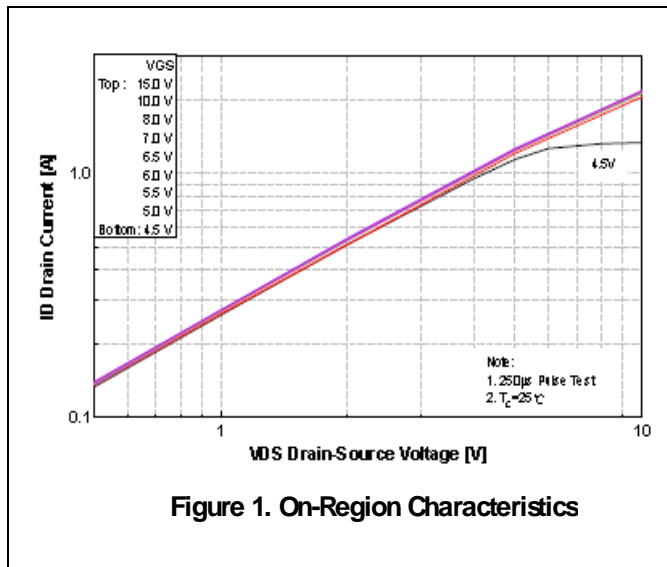
*: Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$

Source-Drain Diode

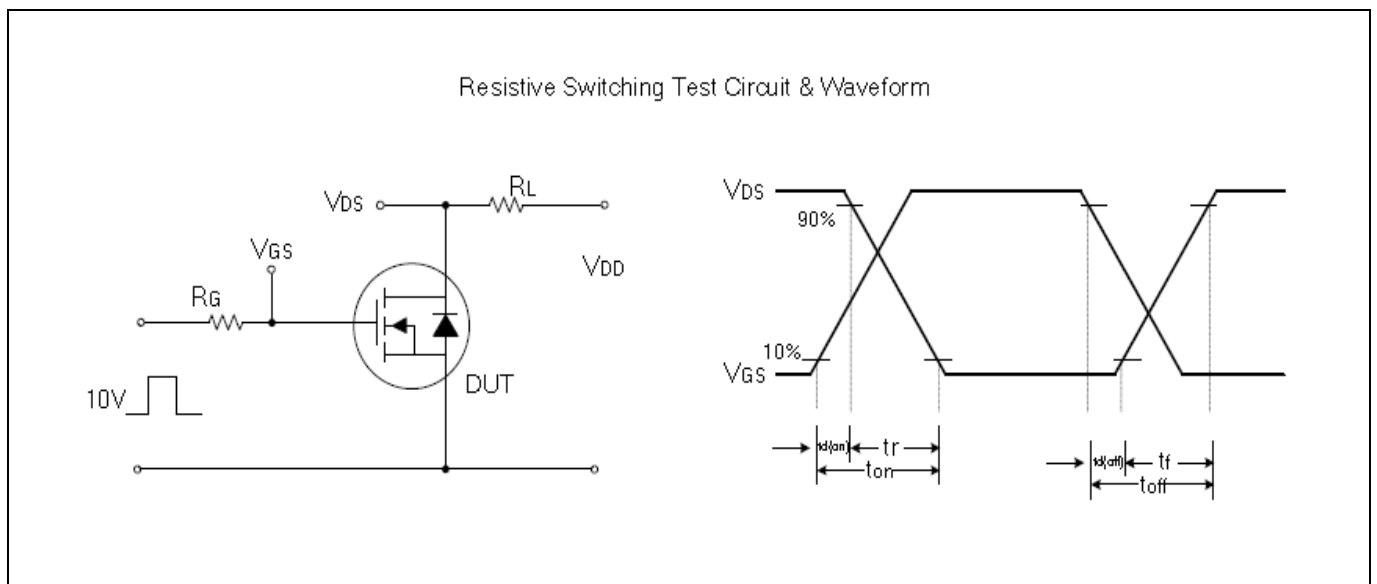
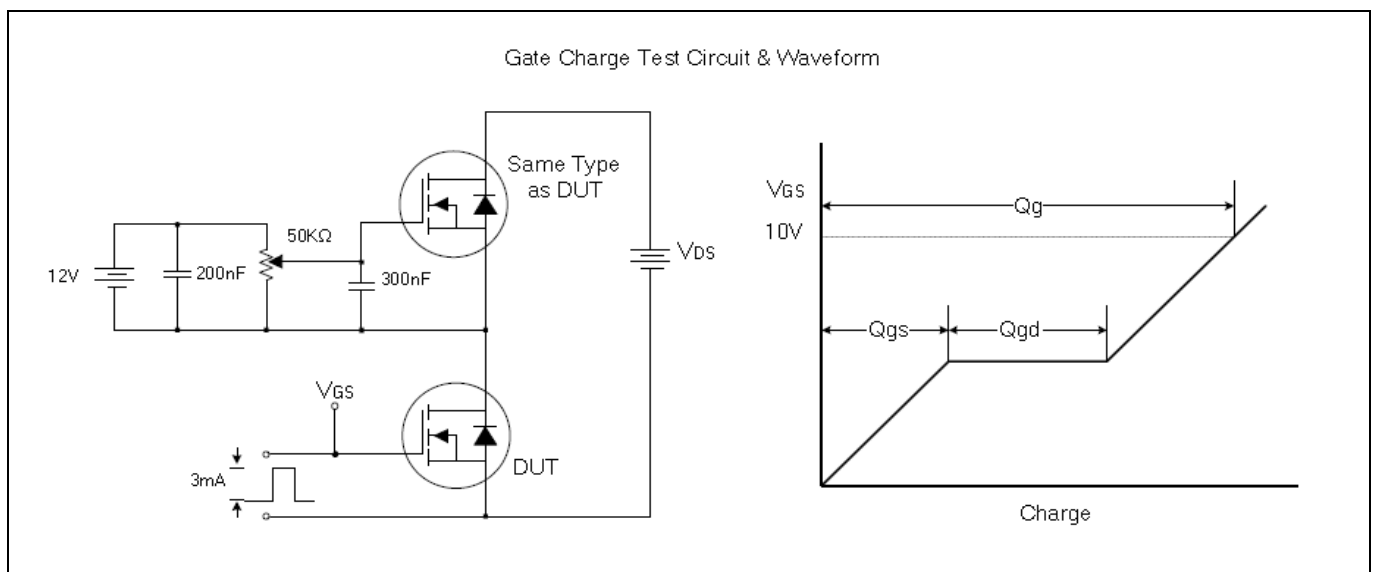
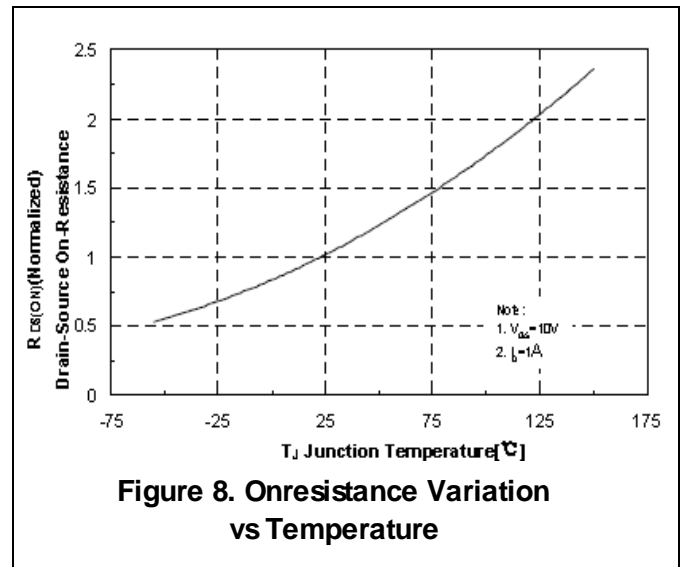
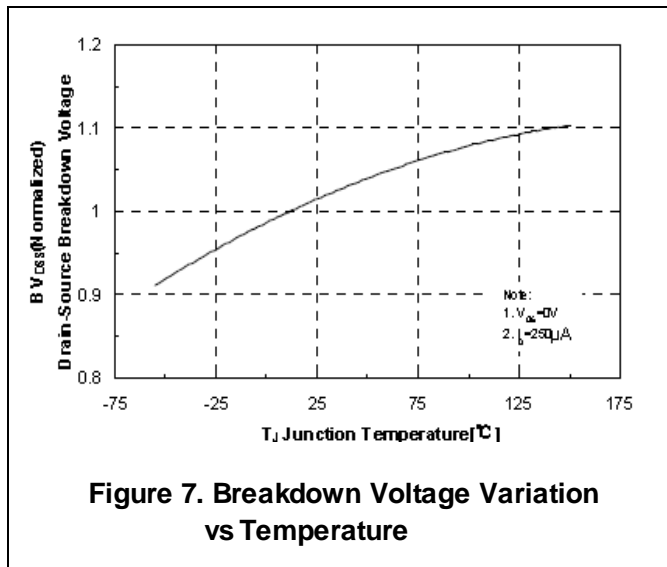
Symbol	Characteristic	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage(1)	-	-	1.4	V
t_{rr}	Reverse Recovery Time	-	300	-	ns
Q_{rr}	Reverse Recovery Charge	-	2.2	-	μC

** : Negligible, Dominated by circuit inductance

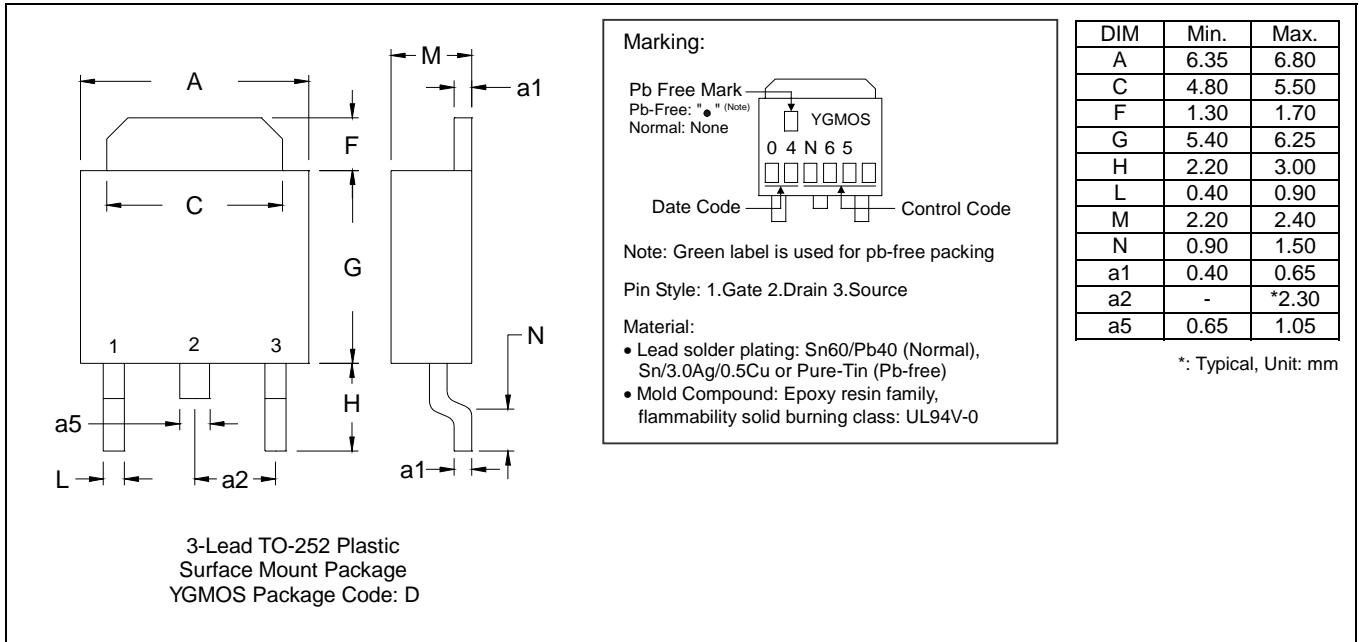
Characteristics Curve



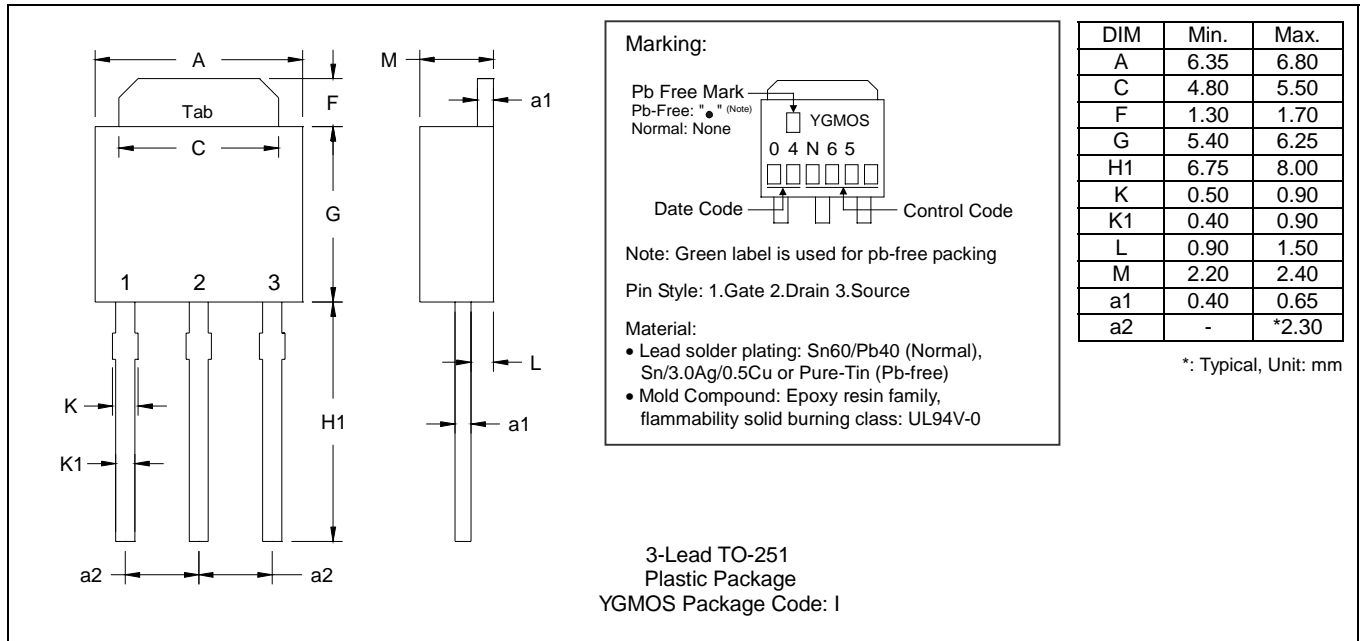
Characteristics Curve



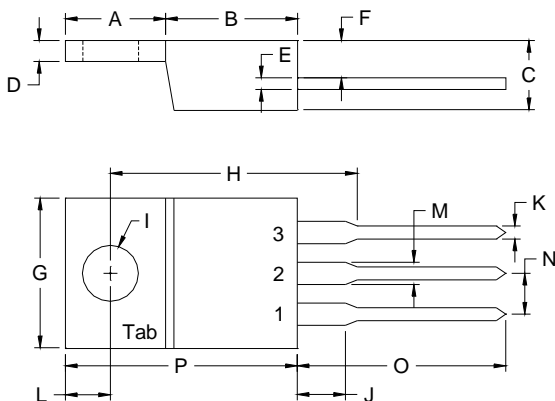
TO-252 Dimension



TO-251 Dimension

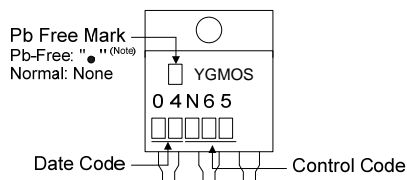


TO-220AB Dimension



3-Lead TO-220AB
 Plastic Package
 YGMOS Package Code: E

Marking:



Note: Green label is used for pb-free packing

Pin Style: 1. Gate 2 & Tab. Drain 3. Source

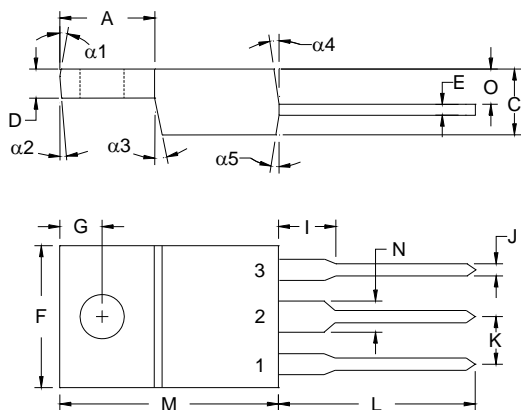
Material:

- Lead solder plating: Sn60/Pb40 (Normal), Sn/3.0Ag/0.5Cu or Pure-Tin (Pb-free)
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

DIM	Min.	Max.
A	5.58	7.49
B	8.38	8.90
C	4.40	4.70
D	1.15	1.39
E	0.35	0.60
F	2.03	2.92
G	9.66	10.28
H	-	*16.25
I	-	*3.83
J	3.00	4.00
K	0.75	0.95
L	2.54	3.42
M	1.14	1.40
N	-	*2.54
O	12.70	14.27
P	14.48	15.87

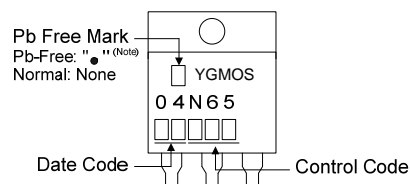
*: Typical, Unit: mm

TO-220FP Dimension



3-Lead TO-220FP
 Plastic Package
 YGMOS Package Code: F

Marking:



Note: Green label is used for pb-free packing

Pin Style: 1. Gate 2. Drain 3. Source

Material:

- Lead solder plating: Sn60/Pb40 (Normal), Sn/3.0Ag/0.5Cu or Pure-Tin (Pb-free)
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

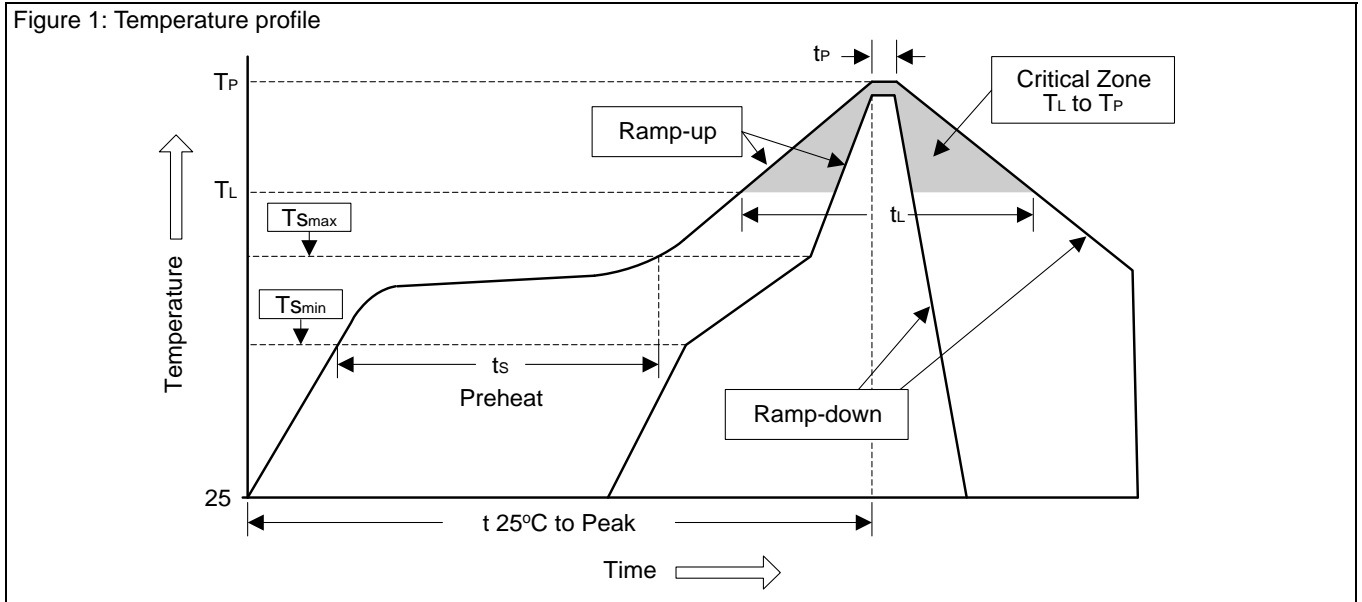
DIM	Min.	Max.
A	6.48	7.40
C	4.40	4.90
D	2.34	3.00
E	0.45	0.80
F	9.80	10.36
G	3.10	3.60
I	2.70	3.43
J	0.60	1.00
K	2.34	2.74
L	12.48	13.60
M	15.67	16.20
N	0.90	1.47
O	2.00	2.96
$\alpha 1/2/4/5$	-	*5°
$\alpha 3$	-	*27°

*: Typical, Unit: mm

Soldering Methods for YGMOS's Products

1. Storage environment: Temperature=10°C~35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices

Figure 1: Temperature profile



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (T_{Smin})	100°C	150°C
- Temperature Max (T_{Smax})	150°C	200°C
- Time (min to max) (t_s)	60~120 sec	60~180 sec
T_{Smax} to T_L		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T_L)	183°C	217°C
- Time (t_L)	60~150 sec	60~150 sec
Peak Temperature (T_P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t_P)	10~30 sec	20~40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak temperature	Dipping time
Pb devices.	245°C ±5°C	10sec ±1sec
Pb-Free devices.	260°C ±5°C	10sec ±1sec